

## **MJE200**

#### **Feature**

- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product :  $f_T=65MHz @ I_C=100mA (Min.)$
- Complement to MJE210



# **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	40	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V	
V <sub>EBO</sub>	Emitter- Base Voltage	8	V	
I <sub>C</sub>	Collector Current	5	Α	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	15	W	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C	

## **Electrical Characteristics** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	25		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =40V, I <sub>E</sub> =0		100	nA
		V <sub>CB</sub> =40V, I <sub>E</sub> =0 @ T <sub>J</sub> =125°C		100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE}=8V$ , $I_{C}=0$		100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =1V, I <sub>C</sub> =500mA	70		
		V <sub>CE</sub> =1V, I <sub>C</sub> =2A	45	180	
		$V_{CE}$ =2V, $I_{C}$ =5A	10		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.3	V
		I <sub>C</sub> =2A, I <sub>C</sub> =200mA		0.75	V
		I <sub>C</sub> =5A, I <sub>B</sub> =1A		1.8	V
V <sub>BE</sub> (sat)	Base- Emitter Saturation Voltage	I <sub>C</sub> =5A, I <sub>B</sub> =1A		2.5	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> =1V, I <sub>C</sub> =2A		1.6	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =100mA	65		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz		80	pF

# **Typical Characteristics**

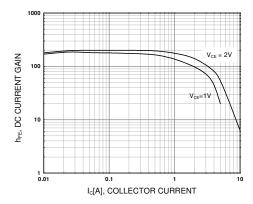


Figure 1. DC current Gain

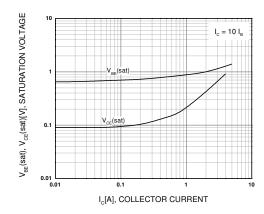


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

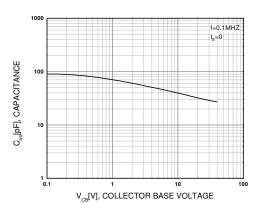


Figure 3. Collector Output Capacitance

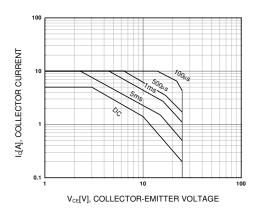


Figure 4. Safe Operating Area

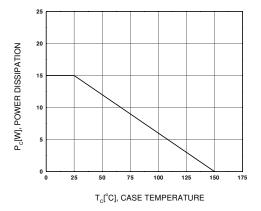
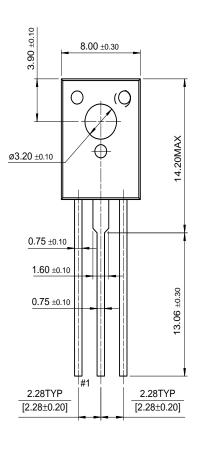


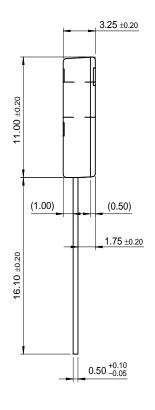
Figure 5. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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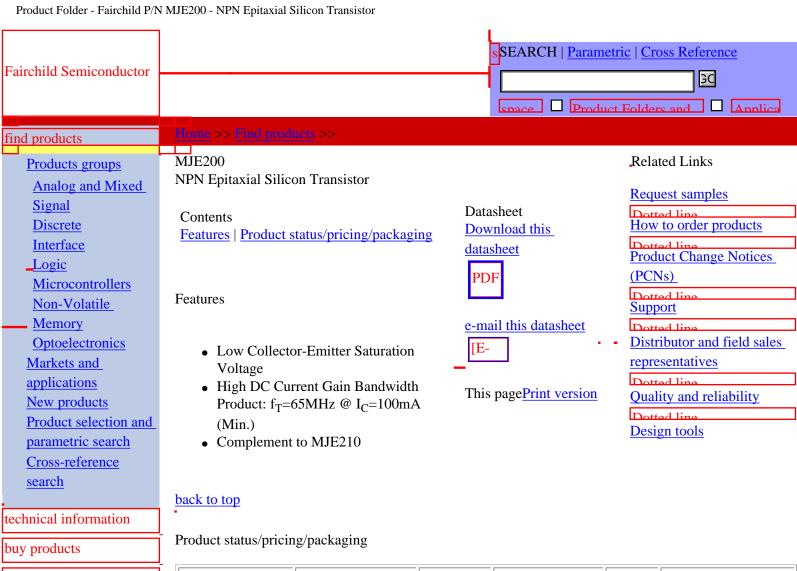
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Product	Product status	Pricing*	Package type	Leads	Packing method
MJE200TSTU	Full Production	N/A	<u>TO-126</u>	3	RAIL
MJE200STU	Full Production	\$0.159	<u>TO-126</u>	3	RAIL

<sup>\* 1,000</sup> piece Budgetary Pricing

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